



2818

PATENT

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May 5, 2003
Date

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants : Michael Nuttall and
Garry Anthony Mercaldi

Attorney Docket No.: 500803.02

Serial No. : 10/075,640

Group Art Unit : 2818

Filed : February 13, 2002

Examiner : David Vu

Title : METHOD FOR ENHANCING VERTICAL GROWTH DURING THE SELECTIVE
FORMATION OF SILICON, AND STRUCTURES FORMED USING SAME

6/B
G. S. Study
5-13-03

Mail Stop Non-Fee Amendment
Commissioner of Patents
P.O. Box 1450
Alexandria, VA 22313-1450

AMENDMENT

Sir:

Please amend the above-captioned patent application as follows:

In the Claims:

Please cancel claims 30-37 and 39-44.

Please amend claim 38 as follows:

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38. (Once Amended) An in-process substrate structure including a plurality of contact regions and a plurality of non-contact regions adjacent the contact regions on a surface of the substrate, the in-process substrate structure comprising:

a selectively formed contact on each contact region, each contact being isolated from contacts on adjacent contact regions.

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